

**RoHS** COMPLIANT

HALOGEN

FREE

Vishay Siliconix

## N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)		
60	0.011 at V <sub>GS</sub> = 10 V	12.7		
	0.013 at V <sub>GS</sub> = 6.0 V	11.7		

#### FEATURES

- Halogen-free According to IEC 61249-2-21
  Definition
- TrenchFET<sup>®</sup> Power MOSFETs
- 175 °C Maximum Junction Temperature
- Compliant to RoHS Directive 2002/95/EC

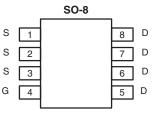
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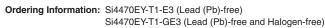
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N-Channel MOSFET

#### **APPLICATIONS**

• Primary Side Switch





ABSOLUTE MAXIMUM RATINGS	(T <sub>A</sub> = 25 °C, unle	ess otherwise	noted)		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	60		V
Gate-Source Voltage		V <sub>GS</sub>	± 20		
	T <sub>A</sub> = 25 °C	– I <sub>D</sub>	12.7	9.0	
Continuous Drain Current $(T_J = 150 \ ^{\circ}C)^a$	T <sub>A</sub> = 70 °C		10.6	7.5	
Pulsed Drain Current		I <sub>DM</sub>	50		А
Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	50		
Continuous Source Current (Diode Conduction) <sup>a</sup>		۱ <sub>S</sub>	3.1	1.5	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	– P <sub>D</sub>	3.75	1.85	w
	T <sub>A</sub> = 70 °C		2.6	1.3	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175		°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
	t ≤ 10 s	- R <sub>thJA</sub> R <sub>thJF</sub>	33	40	°C/W	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		65	80		
Maximum Junction-to-Foot (Drain)	Steady State		17	21		

Notes:

a. Surface mounted on 1" x 1" FR4 board.

Top View ering Information: Si4470EY-T1-E Si4470EY-T1-C BSOLUTE MAXIMUN rameter in-Source Voltage

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static			•				
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2.0			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$			1		
		$V_{DS} = 48$ V, $V_{GS} = 0$ V, $T_{J} = 55$ °C			5	μA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	50			А	
Drain-Source On-State Resistance <sup>a</sup>	Б	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 12 A		0.009	0.011	0	
	R <sub>DS(on)</sub>	$V_{GS} = 6.0 \text{ V}, \text{ I}_{D} = 10 \text{ A}$		0.0105	0.013	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 10 \text{ A}$		50		S	
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	$I_{S} = 3.0 \text{ A}, V_{GS} = 0 \text{ V}$		0.75	1.2	V	
Dynamic <sup>b</sup>	II			1			
Total Gate Charge	Qg			46	70	nC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 30$ V, $V_{GS} = 10$ V, $I_{D} = 12$ A		11.5			
Gate-Drain Charge	Q <sub>gd</sub>			11.5		1	
Gate Resistance	Rg		0.25	0.85	1.4	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			16	25		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 30 V, $R_L$ = 30 $\Omega$		12	18	ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	$\text{I}_{\text{D}}\cong$ 1.0 A, $\text{V}_{\text{GEN}}$ = 10 V, $\text{R}_{\text{g}}$ = 6 $\Omega$		50	75		
Fall Time	t <sub>f</sub>			30	45		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 3.0 A, dl/dt = 100 A/μs		40	60		

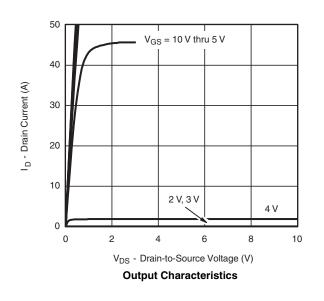
Notes:

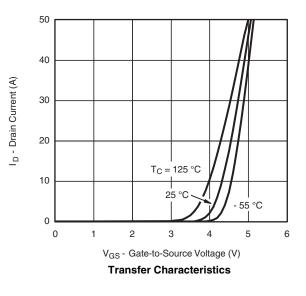
a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





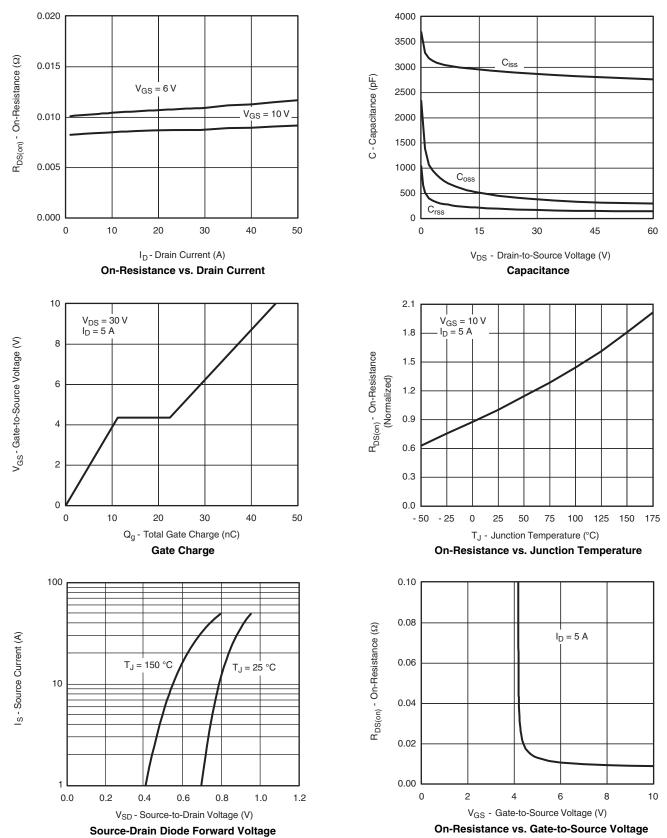
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# Si4470EY

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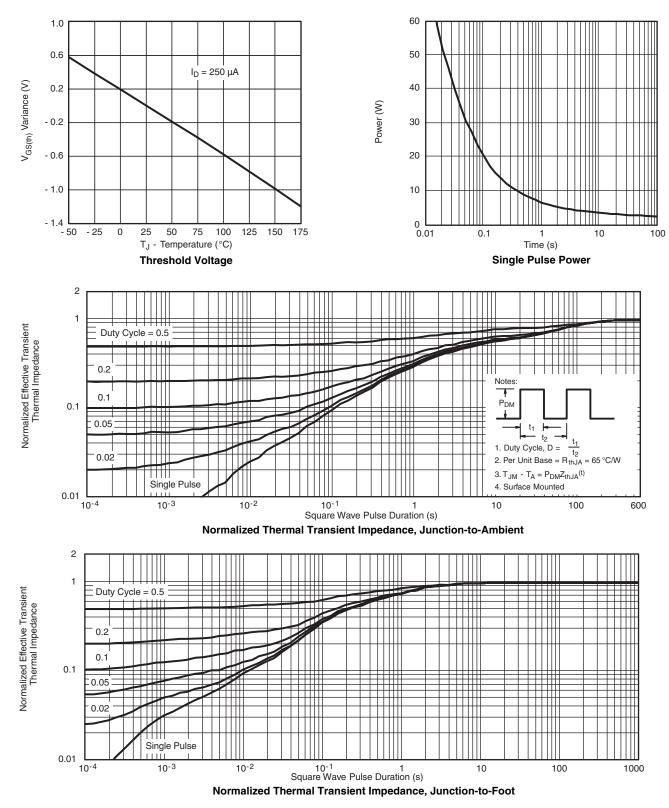
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## Si4470EY

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#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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